

# Global GaN Power Devices Market to Surpass US\$ 2.20 Billion by 2025

*Increasing Demand for High Breakdown Voltage, High Speed Switching, and Miniaturized Semiconductor Components*

SEATTLE, WASHINGTON, UNITED STATES, January 10, 2018 /EINPresswire.com/ -- The [GaN power devices market](#) was valued at US\$ 330.2 million in 2016 and is projected to reach US\$ 2,198.9 million by 2025, exhibiting a CAGR of 23.5% over the forecast period, according to the Global GaN Power Device Market Report, by Device Type (Power Device, RF Power Device), by Voltage Range (<200V, 200-600V, >600V), by Application (Power Drives, Supply and Inverter, Radio Frequency), by Vertical (Telecommunications, Industrial, Automotive, Renewables, Consumer and Enterprise, Medical, Military, and Defense, & Aerospace), published by Coherent Market Insights.



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Gallium nitride is material utilized in the manufacturing of semiconductor power systems, RF components, and light emitting diodes (LEDs). Use of these materials has evolved from discrete transistor outline package (TO) to surface mount devices, to co-packaged solutions with driver on the same chip. This in turn is expected to present strong growth landscape for the GaN power device market over the forecast period.

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Key Trends and Analysis of the Global GaN Power Devices Market:

Among device types, the RF power devices segment held a dominant position in the market in 2016, predominantly owing to the increasing demand for high switching capacities at frequencies, including ultrahigh frequency (UHF), very high frequency (VHF), and microwave bandwidths at optimum energy efficiency and minimum losses during switching transitions.

Moreover, increasing demand for GaN power devices in the defense industry for applications such as radar, communications, and electronic warfare is in turn, expected to boost growth of the GaN power devices market over the forecast period. For instance, in December 2017, U.S. Air Force Research Laboratory (AFRL) developed a new method to amplify signals in wearable devices, featuring flexible sensors and radars, enabling efficient communication.

Among applications, the power drives segment is projected to witness highest CAGR over the forecast period. High total addressable market (TAM) for electrical distribution systems, industrial systems, turbines, industrial control systems, computing systems, and increasing demand for enhanced energy conservation is expected to garner significant growth of the segment.

Among verticals, the telecommunication segment holds the highest market share. The recent past has witnessed advancements in the development of 5G networking technologies, prominently in the U.S., South Korea, Turkey, Japan, and China, and is expected to be commercialized by 2019-2020. This in turn is expected to increase demand for gallium nitride components due to its inherent features of high conductivity, low power loss in switching transitions, and wide band gap of 3.4 eV. Thus, the telecommunication segment is expected to hold a dominant position in the global GaN power devices market over the forecast period.

#### Key Takeaways of the Market:

Among geography, Asia Pacific is expected to hold a dominant position in the global GaN power devices market, witnessing the highest CAGR over the forecast period. Proliferation of electric vehicles (EVs) and the development of renewable energy sources to reduce the negative impact of conventional energy sources on the environment, is expected to boost growth of the market in the region. For instance, in January 2018, the Government of China extended its tax rebates and incentive plans for hybrid and plug-in electric vehicles, till 2020. Moreover, according to Mineral Commodity Summaries, 2016, by the U.S. Department of the Interior and Geological Survey, China accounted for around 83% of the global low-grade gallium production, of which over 70% was utilized for GaAs and GaN wafers that are used in ICs and optoelectronic devices. Other major economies such as Japan, India, South Korea, and ASEAN countries are expected to account for a significant market share.

To know the latest trends and insights prevalent in this market, click the link below:

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Browse 60 market data tables\* and 40 figures\* on "Global GaN Power Device Market" - Global forecast to 2025.

Some of the major players in the global GaN power devices market are Cree Inc., Efficient Power Conversion (EPC) Corporation, Infineon Technologies, GaN Systems Inc., Macom, Microsemi Corporation, Mitsubishi Electric Corporation, Navitas Semiconductor, Qorvo, Inc., and Toshiba Electronic Devices & Storage Corporation.

#### About Coherent Market Insights:

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